

**KSR2001**

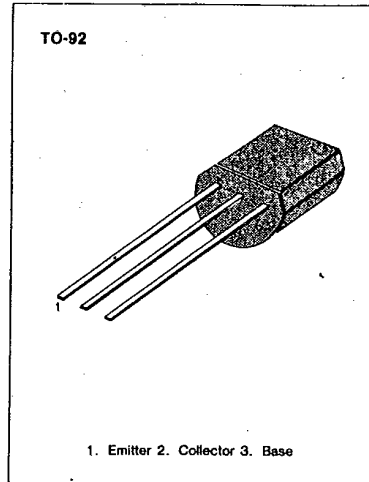
**PNP EPITAXIAL SILICON TRANSISTOR**

**SWITCHING APPLICATION** (Bias Resistor Built In)

- Switching circuit, inverter, interface circuit Driver circuit
- Built in bias Resistor ( $R_1=4.7K\Omega$ ,  $R_2=4.7K\Omega$ )
- Complement to KSR1001

**ABSOLUTE MAXIMUM RATINGS** ( $T_a=25^\circ C$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-10	V
Collector Current	$I_C$	-100	mA
Collector Dissipation	$P_C$	300	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 - 150	$^\circ C$

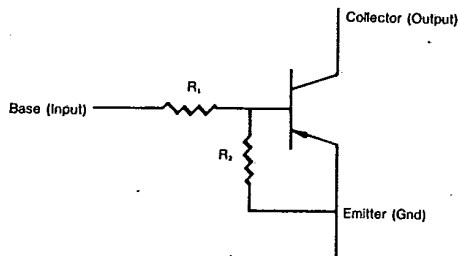


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**ELECTRICAL CHARACTERISTICS** ( $T_a=25^\circ C$ )

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C=-10\mu A, I_E=0$	-50			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=-100\mu A, I_B=0$	-50			V
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=-40V, I_E=0$			-0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=-5V, I_C=-10mA$	20			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-0.5mA$			-0.3	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE}=-5mA, I_C=-10V$		200		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0$ $f=1.0MHz$		5.5		pF
Input Off Voltage	$V_i(off)$	$V_{CE}=-5V, I_C=-100\mu A$	-0.5			V
Input On Voltage	$V_i(on)$	$V_{CE}=-0.3V, I_C=-20mA$			-3	V
Input Resistor	$R_1$		3.2	4.7	6.2	K $\Omega$
Resistor Ratio	$R_1/R_2$		0.9	1	1.1	

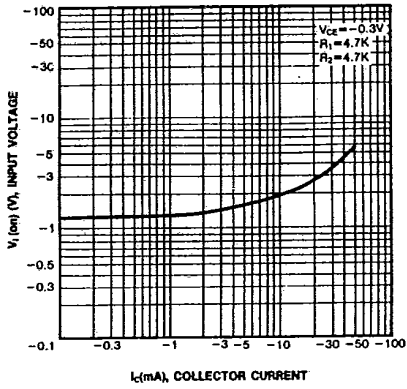
**Equivalent Circuit**



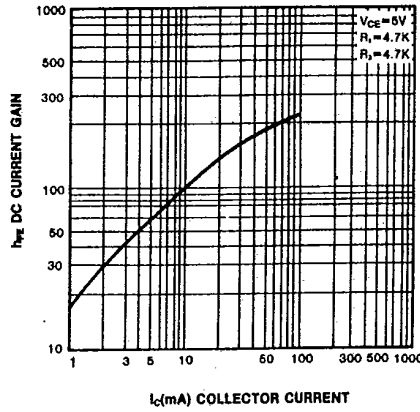
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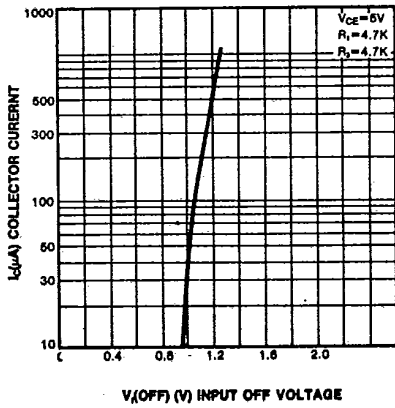
INPUT ON VOLTAGE



DC CURRENT GAIN



INPUT OFF VOLTAGE



POWER DERATING

